



Quasi-Ternary System $\text{Ag}_2\text{Se}-\text{GeSe}_2-\text{As}_2\text{Se}_3$

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Submitted: 25 October 2021 / in revised form: 30 July 2022 / Accepted: 2 August 2022 / Published online: 7 September 2022
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Abstract Phase equilibria in the quasi-ternary system $\text{Ag}_2\text{Se}-\text{GeSe}_2-\text{As}_2\text{Se}_3$ were investigated by direct synthesis, x-ray phase, differential thermal and microstructural analysis methods. Isothermal section of the system at 513 K (240 °C) was constructed, the existence of ternary compounds Ag_8GeSe_6 , Ag_3AsSe_3 , AgAsSe_2 , AgAs_3Se_5 was confirmed, and the existence of quaternary compounds was not found. Three quasi-binary phase diagrams $\text{Ag}_2\text{Se}-\text{As}_2\text{Se}_3$, $\text{Ag}_8\text{GeSe}_6-\text{AgAsSe}_2$, $\text{GeSe}_2-\text{AgAsSe}_2$, three vertical sections $\text{Ag}_8\text{GeSe}_6-\text{Ag}_3\text{AsSe}_3$, $\text{Ag}_8\text{GeSe}_6-\text{As}_2\text{Se}_3$, $\text{GeSe}_2-\text{AgAs}_3\text{Se}_5$, and the liquidus surface projection onto the concentration triangle were constructed. The regions of primary crystallization of phases, character, temperature, and coordinates of mono- and invariant equilibria were determined.

Keywords chalcogenides · isothermal section · liquidus surface projection · microstructural analysis · phase equilibria · thermal analysis · x-ray powder diffraction

1 Introduction

The binary compounds Ag_2Se , GeSe_2 , As_2Se_3 melt congruently at 1170 K (897 °C), 1013 K (740 °C), and 648 K (375 °C)^[1], respectively, possess insignificant homogeneity regions and may serve as components of the quasi-ternary system $\text{Ag}_2\text{Se}-\text{GeSe}_2-\text{As}_2\text{Se}_3$. The study of this quasi-ternary system is of current interest because it is formed by binary compounds with important semiconducting properties. Complex chalcogenide semiconductors attract growing interest in materials science due to their prospects for use as materials in the fields of nonlinear optics, optoelectronics, and acousto-optics.^[2–6]

Phase equilibria in the quasi-binary system $\text{Ag}_2\text{Se}-\text{GeSe}_2$ were studied in Ref 7–10. The authors of Ref 10 confirmed the existence of one ternary compound Ag_8GeSe_6 which melts congruently at 1175 K (902 °C) and undergoes two polymorphous transformations at 269 K (–4 °C)^[7] and 321 K (48 °C),^[7,9,10] respectively. The eutectic points coordinates were ascertained as 1103 K (830 °C), 15 mol.% GeSe_2 and 843 K (570 °C), 56 mol.% GeSe_2 ,^[10] and agree well with Ref 7. γ - Ag_8GeSe_6 which is stable at room temperature crystallizes in space group, S.G. $Pmn2_1$, with lattice parameters $a = 0.7823$ nm, $b = 0.7712$ nm, $c = 1.0885$ nm.^[11]

The $\text{Ag}_2\text{Se}-\text{As}_2\text{Se}_3$ phase diagram was described in Ref 12–14. According to Ref 14, the existence of three compounds, Ag_3AsSe_3 , AgAsSe_2 and AgAs_3Se_5 , was established in the system. The AgAs_3Se_5 compound forms incongruently at 643 K (370 °C) and has a eutectic with As_2Se_3 at 87 mol.% As_2Se_3 and 630 K (357 °C). The AgAsSe_2 compound melts congruently at 673 K (400 °C) and does not have a polymorphous transformation (whereas according to Ref 13 there is a polymorphous transformation of AgAsSe_2 at 658 K (385 °C)). The peritectic reaction $L + \text{Ag}_2\text{Se} \leftrightarrow \text{Ag}_3\text{AsSe}_3$ takes place at 663 K

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(390 °C). The coordinates of the eutectic of Ag_3AsSe_3 – AgAsSe_2 are 33 mol.% As_2Se_3 and 653 K (380 °C).

The crystal structure of the Ag_3AsSe_3 compound was determined in Ref 13, 15. The compound is an analogue of the proustite mineral (Ag_3AsS_3), crystallizes in S.G. $R\bar{3}c$; and has lattice parameters $a = 1.1285$ nm, $c = 0.8803$ nm [13], or $a = 1.1298$ nm, $c = 0.8757$ nm [15]. For the high-temperature modification (HTM) of AgAsSe_2 , the authors of Ref 13 determined the crystal structure S.G. $R\bar{3}m$, structure type NaCrS_2 , $a = 0.3915$ nm, $c = 2.0375$ nm. The diffraction pattern of the low-temperature modification (LTM) of AgAsSe_2 was indexed by the authors of Ref 13 in the primitive tetragonal cell with $a = 1.2548$ nm, $c = 1.1140$ nm. The compound AgAs_3Se_5 crystallizes in S.G. $R\bar{3}m$, $a = 0.38195(1)$ nm, $c = 5.0082(2)$ nm [16].

Phase diagram of the GeSe_2 – As_2Se_3 system of the eutectic type, with the eutectic point at 20 mol.% GeSe_2 and 618 K (345 °C) [17].

2 Experimental Methods

Phase equilibria in the quasi-ternary system Ag_2Se – GeSe_2 – As_2Se_3 were studied using 122 samples. The alloys were synthesized by direct single-temperature method from high-purity elements (Ag 99.995, Ge 99.99, Se 99.9997, As 99.9999 wt.%) in quartz containers that were evacuated to a residual pressure of 0.133 Pa and sealed. The synthesis was performed in a shaft-type furnace with temperature control with an accuracy of ± 5 K (± 5 °C). The maximum synthesis temperature was 1373 K (1100 °C), the heating and cooling rate was 10 K/h (10 °C/h). Homogenization annealing at 513 K (240 °C) was held for 600 h, after which the samples were quenched into 25% aqueous NaCl solution.

The as-obtained samples were investigated by x-ray diffraction (XRD) method (DRON 4–13 diffractometer, CuK_α radiation, $10(2\theta)^\circ < 2\theta < 90^\circ$, 0.05° scan step, 1–5 s exposure in each point) and differential thermal analysis (DTA) (“Thermodent H307/1” furnace with a PDA-1 XY-recorder, Pt/Pt–Rh thermocouple). The two-phase or three-phase composition of the samples was also checked by the microstructure analysis (MSA), which was performed on a PMT-3 M microhardness tester.

3 Results and Discussion

3.1 Isothermal Section of the Quasi-Ternary System Ag_2Se – GeSe_2 – As_2Se_3 at 513 K (240 °C)

According to XRD and MSA results of 122 samples (Fig. 1), isothermal section of the Ag_2Se – GeSe_2 –

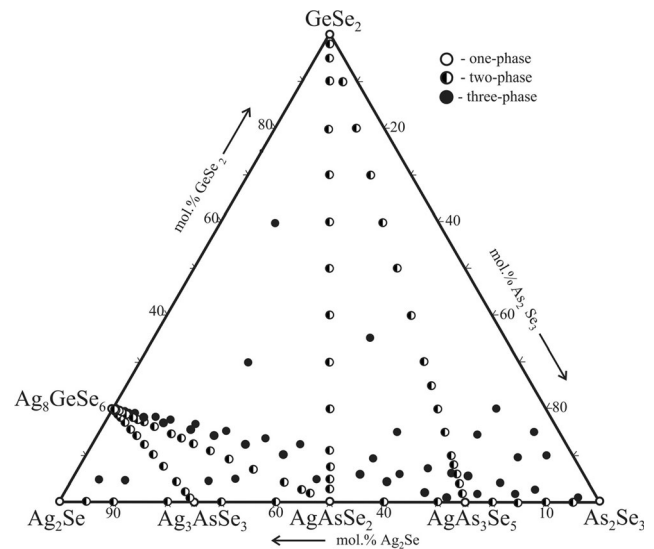


Fig. 1 Chemical and phase compositions of the Ag_2Se – GeSe_2 – As_2Se_3 system samples at 513 K

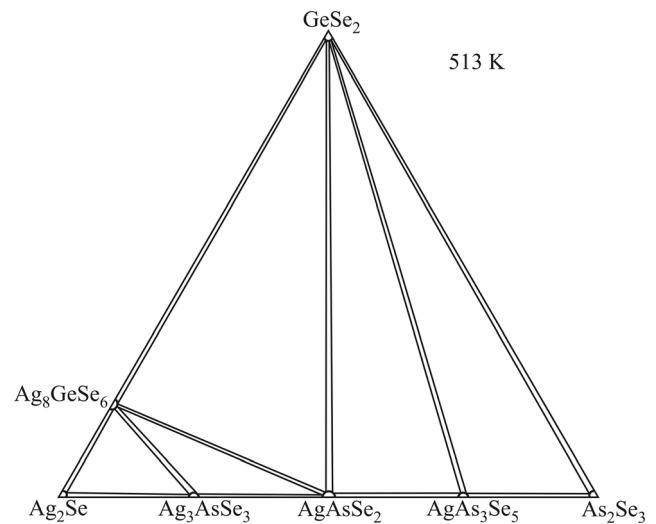


Fig. 2 Isothermal section of the quasi-ternary system Ag_2Se – GeSe_2 – As_2Se_3 at 513 K

As_2Se_3 system at 513 K was plotted (Fig. 2). Diffraction patterns of the binary compounds were indexed (Fig. 3): GeSe_2 by S.G. $P2_1/c$, $a = 0.7007(2)$ nm, $b = 1.6819(5)$ nm, $c = 1.1806(3)$ nm, $\beta = 90.74(2)^\circ$; As_2Se_3 in S.G. $P2_1/n$, $a = 1.2794(7)$ nm, $b = 0.9874(5)$ nm, $c = 0.4267(2)$ nm, $\alpha = 90.96(4)^\circ$, and agree well with the literature data from Ref 18–20, respectively. The existence of the four ternary compounds Ag_8GeSe_6 , Ag_3AsSe_3 , LTM- AgAsSe_2 , AgAs_3Se_5 was confirmed (Fig. 3). The diffraction pattern of the Ag_8GeSe_6 compound was indexed with the orthorhombic S.G. $Pmn2_1$, $a = 0.78443(5)$ nm, $b = 0.77372(5)$ nm, $c = 1.09141(7)$ nm, which is consistent with Ref 11. The diffraction pattern of Ag_3AsSe_3 was

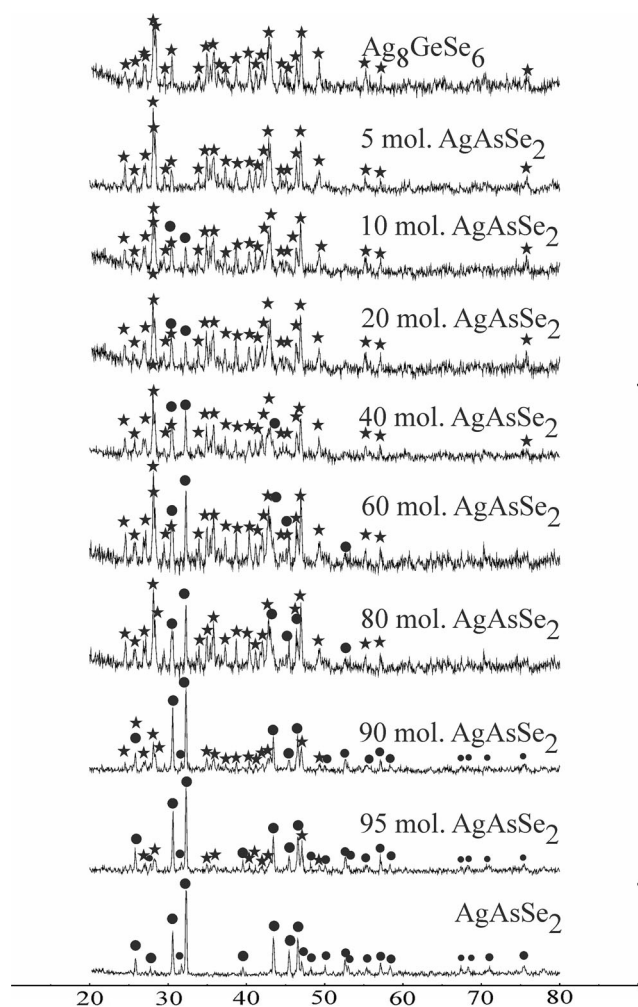


Fig. 4 Experimental diffractograms of the samples of the Ag_8GeSe_6 – AgAsSe_2 system (compositions are given in mol.%)

3.2 The Quasi-Binary System Ag_2Se – As_2Se_3

Due to somewhat differing literature data in Ref 12–14, we re-investigated the Ag_2Se – As_2Se_3 system (Fig. 5). The compositions of the samples for the investigation are given in Table 1. Phase diagram of the system was plotted from the results of XRD, DTA (Table 1) and MSA. The existence and formation mechanism of three compounds Ag_3AsSe_3 , AgAsSe_2 and AgAs_3Se_5 , and the polymorphous transformation of AgAsSe_2 were confirmed. Ag_3AsSe_3 melts incongruently at 660 K (387 °C), AgAsSe_2 melts congruently at 683 K (410 °C), and AgAs_3Se_5 melts incongruently at 644 K (371 °C). The horizontal line at 635 K (362 °C) corresponds to the eutectic reaction $L_{e1} \leftrightarrow \text{AgAs}_3\text{Se}_5 + \text{As}_2\text{Se}_3$ with the eutectic point at 88 mol.% As_2Se_3 . The temperatures of invariant reactions practically do not differ from Ref 15. The phase diagram of the Ag_2Se – As_2Se_3 system shows a horizontal line at 630 K (357 °C) which indicates a polymorphous

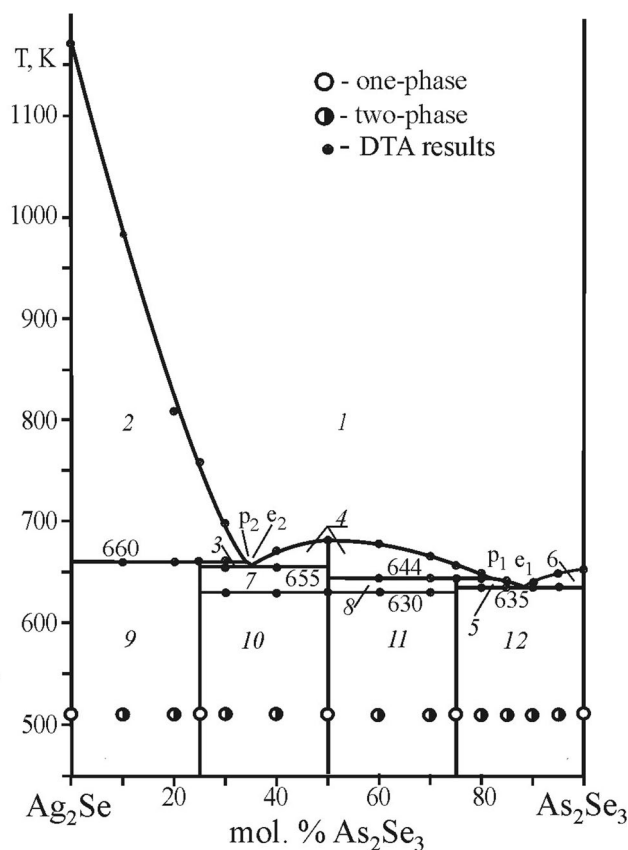


Fig. 5 Phase diagram of the Ag_2Se – As_2Se_3 system: 1–L; 2–L + Ag_2Se , 3–L + Ag_3AsSe_3 , 4–L + HTM- AgAsSe_2 , 5–L + AgAs_3Se_5 , 6–L + As_2Se_3 , 7– Ag_3AsSe_3 + HTM- AgAsSe_2 , 8–HTM- AgAsSe_2 + AgAs_3Se_5 , 9– Ag_2Se + Ag_3AsSe_3 , 10– Ag_3AsSe_3 + LTM- AgAsSe_2 , 11–LTM- AgAsSe_2 + AgAs_3Se_5 , 12– AgAs_3Se_5 + As_2Se_3

transformation of the AgAsSe_2 compound; obtained temperature value is slightly lower than indicated in Ref 12, 13.

3.3 The Quasi-Binary System Ag_8GeSe_6 – AgAsSe_2

Phase diagram of the Ag_8GeSe_6 – AgAsSe_2 system (Fig. 6) is based on DTA, XRD and MSA results. The axes of the isothermal section (Fig. 1 and 2) and the liquidus projection (Fig. 12) are in mol.% of the components, Ag_2Se , As_2Se_3 and GeSe_2 , while the axes of the vertical sections (Figs. 6–11) are in mol.% of the compounds constituting these sections. For easier correlation with the isothermal section and the liquidus projection, a secondary axis with mol.% of As_2Se_3 is added to the diagram. The compositions of the synthesized samples as well as DTA results are given in Table 2. Some of the DTA curves are shown in Fig. 7. They were measured from and till the temperature of annealing of the samples, 513 K. The investigated system is of the eutectic type. The eutectic point coordinates

Table 1 Compositions of the samples of the $\text{Ag}_2\text{Se}-\text{As}_2\text{Se}_3$ quasi-binary system and their DTA results

| No. | Composition, mol. % | T, K |
|-----|--|----------------------------|
| 1 | Ag_2Se | 1170 |
| 2 | 90 Ag_2Se -10 As_2Se_3 | 983 ; 660 |
| 3 | 80 Ag_2Se -20 As_2Se_3 | 810 ; 660 |
| 4 | 75 Ag_2Se -25 As_2Se_3 | 757 ; 660 |
| 5 | 70 Ag_2Se -30 As_2Se_3 | 697 ; 660; 655; 630 |
| 6 | 60 Ag_2Se -40 As_2Se_3 | 670 ; 655; 630 |
| 7 | 50 Ag_2Se -50 As_2Se_3 | 683 ; 630 |
| 8 | 40 Ag_2Se -60 As_2Se_3 | 675 ; 644; 630 |
| 9 | 30 Ag_2Se -70 As_2Se_3 | 665 ; 644; 630 |
| 10 | 25 Ag_2Se -75 As_2Se_3 | 657 ; 644 |
| 11 | 20 Ag_2Se -80 As_2Se_3 | 650 ; 644; 635 |
| 12 | 15 Ag_2Se -85 As_2Se_3 | 642 ; 635 |
| 13 | 10 Ag_2Se -90 As_2Se_3 | 640 ; 635 |
| 14 | 5 Ag_2Se -95 As_2Se_3 | 648 ; 635 |
| 15 | As_2Se_3 | 652 |

Bold values indicate the melting temperatures of the samples

Table 2 Compositions of the samples of the $\text{Ag}_8\text{GeSe}_6-\text{AgAsSe}_2$ quasi-binary system calculated through the ternary, binary compounds and their DTA results

| No. | Composition, mol. % | T, K |
|-----|---|------------------------|
| 1 | Ag_8GeSe_6 | 1175 |
| 2 | (80 Ag_2Se -20 GeSe_2 -0 As_2Se_3) | -; 660; 590 |
| 3 | (79.9 Ag_2Se -19.9 GeSe_2 -0.2 As_2Se_3) | 1165 ; 659; 591 |
| 4 | (79.7 Ag_2Se -19.8 GeSe_2 -0.5 As_2Se_3) | 1160 ; 659; 592 |
| 5 | (79.3 Ag_2Se -19.6 GeSe_2 -1.1 As_2Se_3) | 1150 ; 661; 592 |
| 6 | (79.0 Ag_2Se -19.3 GeSe_2 -1.7 As_2Se_3) | 1125 ; 660; 590 |
| 7 | (78.1 Ag_2Se -18.8 GeSe_2 -3.1 As_2Se_3) | 1105 ; 659; 590 |
| 8 | (77.1 Ag_2Se -18.1 GeSe_2 -4.9 As_2Se_3) | 1090 ; 660; 590 |
| 9 | (76.5 Ag_2Se -17.6 GeSe_2 -5.9 As_2Se_3) | 1075 ; 660; 590 |
| 10 | (75.8 Ag_2Se -17.2 GeSe_2 -7.0 As_2Se_3) | 1020 ; 660; 591 |
| 11 | (74.1 Ag_2Se -16.1 GeSe_2 -9.8 As_2Se_3) | 1000 ; 661; 590 |
| 12 | (71.9 Ag_2Se -14.6 GeSe_2 -13.5 As_2Se_3) | 970 ; 659; 590 |
| 13 | (70.5 Ag_2Se -13.6 GeSe_2 -15.9 As_2Se_3) | 935 ; 660; 592 |
| 14 | (68.8 Ag_2Se -12.5 GeSe_2 -18.8 As_2Se_3) | 890 ; 661; 591 |
| 15 | (66.7 Ag_2Se -11.1 GeSe_2 -22.2 As_2Se_3) | 840 ; 660; 592 |
| 16 | (64.1 Ag_2Se -9.4 GeSe_2 -26.6 As_2Se_3) | 765 ; 660; 588 |
| 17 | (60.7 Ag_2Se -7.1 GeSe_2 -32.1 As_2Se_3) | 680 ; 660; 590 |
| 18 | (56.3 Ag_2Se -4.2 GeSe_2 -39.6 As_2Se_3) | 670 ; 660; 590 |
| 19 | (52.8 Ag_2Se -1.9 GeSe_2 -45.4 As_2Se_3) | 675 ; 660; 590 |
| 20 | AgAsSe_2 | 683 ; 630 |

Bold values indicate the melting temperatures of the samples

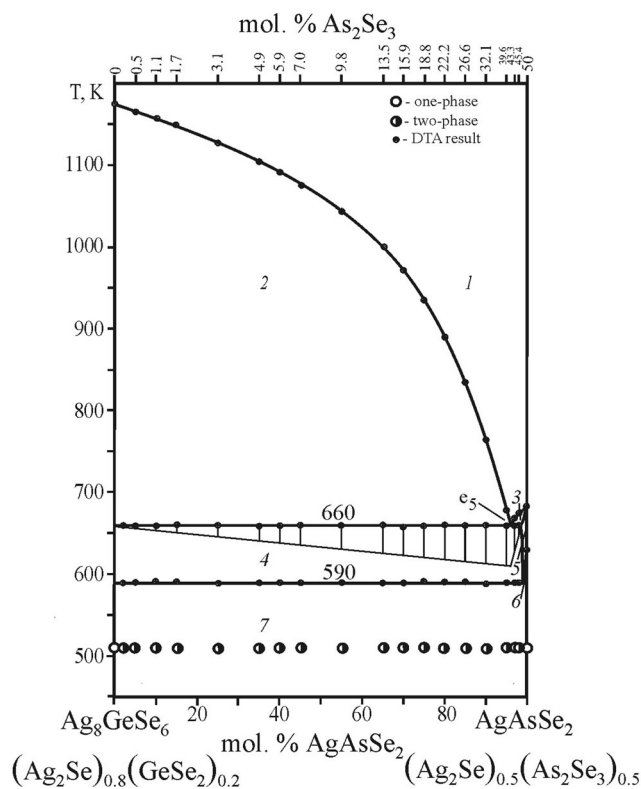


Fig. 6 Phase diagram of the $\text{Ag}_8\text{GeSe}_6-\text{AgAsSe}_2$ system: 1-L, 2-L + Ag_8GeSe_6 , 3-L + HTM- AgAsSe_2 , 4- Ag_8GeSe_6 + HTM- AgAsSe_2 , 5-HTM- AgAsSe_2 , 6-HTM- AgAsSe_2 + LTM- AgAsSe_2 , 7- Ag_8GeSe_6 + LTM- AgAsSe_2

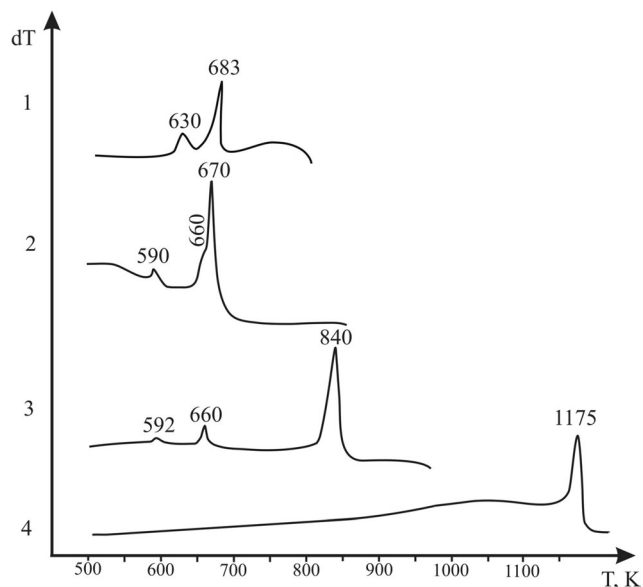


Fig. 7 DTA curves of some alloys of the Ag_8GeSe_6 – AgAsSe_2 system: 1– AgAsSe_2 , 2–97 mol.% AgAsSe_2 – 3 mol.% Ag_8GeSe_6 , 3–85 mol.% AgAsSe_2 – 15 mol.% Ag_8GeSe_6 , 4– Ag_8GeSe_6

were determined by plotting the Tammann triangle according to Ref 21. Point e_5 corresponds to the composition of 4 mol.% Ag_8GeSe_6 –96 mol.% AgAsSe_2 (55.2 mol.% Ag_2Se –3.4 mol.% GeSe_2 –41.4 mol.% As_2Se_3), 660 K (387 °C), where the invariant reaction $L_{e_5} \leftrightarrow \text{Ag}_8\text{GeSe}_6 + \text{HTM-AgAsSe}_2$ takes place. The liquidus is represented by the curves of the primary crystallization of Ag_8GeSe_6 and the solid solution HTM- AgAsSe_2 . The eutectoid reaction $\text{HTM-AgAsSe}_2 \leftrightarrow \text{LTM-AgAsSe} + \text{Ag}_8\text{GeSe}_6$ takes place at 590 K (317 °C). Below this temperature the samples are two-phase, $\text{Ag}_8\text{GeSe}_6 + \text{LTM-AgAsSe}_2$, which was established by XRD (Fig. 4) and MSA methods. No significant solid solubility based on the starting compounds was observed.

3.4 The Vertical Section Ag_8GeSe_6 – Ag_3AsSe_3

The compositions and DTA data of the alloys are given in Table 3. Based on these the vertical section was built. The liquidus (Fig. 8) crosses the primary crystallization regions of Ag_8GeSe_6 (field 2) and Ag_2Se (field 4). The regions of the secondary crystallization of the monovariant eutectic reaction $L_{e_3-U1} \leftrightarrow \text{Ag}_2\text{Se} + \text{Ag}_8\text{GeSe}_6$ (field 3) and the peritectic reaction $L_{p_2-U1} + \text{Ag}_2\text{Se} \leftrightarrow \text{Ag}_3\text{AsSe}_3$ (field 5) descend to the plane of the invariant reaction

Table 3 Compositions of the samples of the Ag_8GeSe_6 – Ag_3AsSe_3 vertical section calculated from the compositions of the ternary, binary compounds and their DTA results

| No | Composition. mol. % | T, K |
|----|--|------------------------|
| 1 | Ag_8GeSe_6 (80 Ag_2Se –20 GeSe_2 –0 As_2Se_3) | 1175 |
| 2 | 98 Ag_8GeSe_6 –2 Ag_3AsSe_3 (79.96 Ag_2Se –19.84 GeSe_2 –0.20 As_2Se_3) | 1170 ; 965; 649 |
| 3 | 95 Ag_8GeSe_6 –5 Ag_3AsSe_3 (79.90 Ag_2Se –19.59 GeSe_2 –0.52 As_2Se_3) | 1162 ; 964; 649 |
| 4 | 90 Ag_8GeSe_6 –10 Ag_3AsSe_3 (79.79 Ag_2Se –19.15 GeSe_2 –1.06 As_2Se_3) | 1150 ; 963; 650 |
| 5 | 80 Ag_8GeSe_6 –20 Ag_3AsSe_3 (79.55 Ag_2Se –18.18 GeSe_2 –2.27 As_2Se_3) | 1126 ; 963; 649 |
| 6 | 70 Ag_8GeSe_6 –30 Ag_3AsSe_3 (79.27 Ag_2Se –17.07 GeSe_2 –3.66 As_2Se_3) | 1105 ; 964; 650 |
| 7 | 60 Ag_8GeSe_6 –40 Ag_3AsSe_3 (78.95 Ag_2Se –15.79 GeSe_2 –5.26 As_2Se_3) | 1080 ; 963; 650 |
| 8 | 50 Ag_8GeSe_6 –50 Ag_3AsSe_3 (78.57 Ag_2Se –14.29 GeSe_2 –7.14 As_2Se_3) | 1162 ; 965; 650 |
| 9 | 40 Ag_8GeSe_6 –60 Ag_3AsSe_3 (78.13 Ag_2Se –12.50 GeSe_2 –9.38 As_2Se_3) | 1040 ; 964; 650 |
| 10 | 30 Ag_8GeSe_6 –70 Ag_3AsSe_3 (77.59 Ag_2Se –10.34 GeSe_2 –12.07 As_2Se_3) | 1010 ; 964; 650 |
| 11 | 20 Ag_8GeSe_6 –80 Ag_3AsSe_3 (76.92 Ag_2Se –7.96 GeSe_2 –15.38 As_2Se_3) | 964 ; 650 |
| 12 | 10 Ag_8GeSe_6 –90 Ag_3AsSe_3 (76.09 Ag_2Se –4.35 GeSe_2 –19.57 As_2Se_3) | 925 ; 785; 650 |
| 13 | 5 Ag_8GeSe_6 –95 Ag_3AsSe_3 (75.58 Ag_2Se –2.33 GeSe_2 –22.09 As_2Se_3) | 882 ; 650 |
| 14 | 2 Ag_8GeSe_6 –98 Ag_3AsSe_3 (75.24 Ag_2Se –0.97 GeSe_2 –23.79 As_2Se_3) | 805 ; 650 |
| 15 | Ag_3AsSe_3 (75 Ag_2Se –0 GeSe_2 –25 As_2Se_3) | 757 ; 660 |

Bold values indicate the melting temperatures of the samples

$L_{U1} + \text{Ag}_2\text{Se} \leftrightarrow \text{Ag}_8\text{GeSe}_6 + \text{Ag}_3\text{AsSe}_3$ which occurs at 650 K (377 °C) and ends with the exhaustion of L and Ag_2Se . Therefore, below 650 K (377 °C) the samples are two-phase $\text{Ag}_8\text{GeSe}_6 + \text{Ag}_3\text{AsSe}_3$ (field 6), which was determined by XRD and MSA data. No solid solubility based on the starting compounds was found.

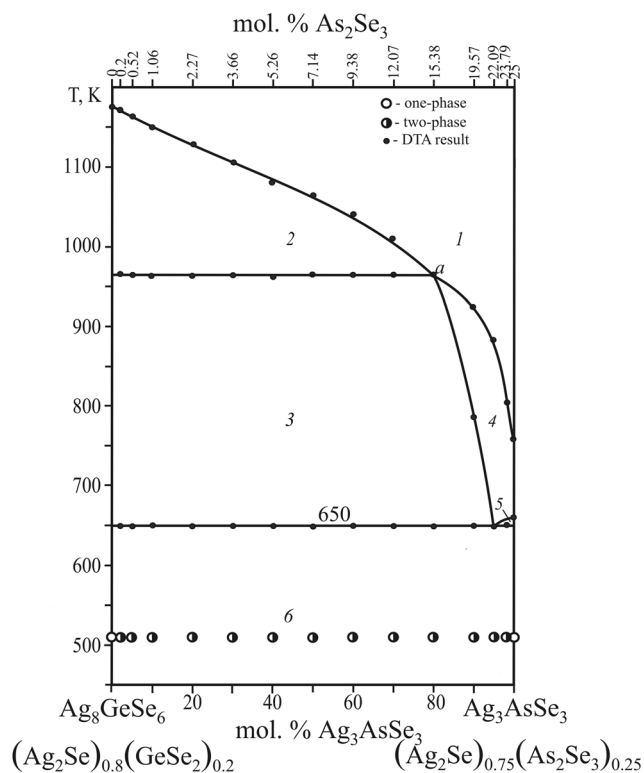


Fig. 8 The vertical section $\text{Ag}_8\text{GeSe}_6\text{--Ag}_3\text{AsSe}_3$: 1–L, 2–L + Ag_8GeSe_6 , 3–L + $\text{Ag}_2\text{Se} + \text{Ag}_8\text{GeSe}_6$, 4–L + Ag_2Se , 5–L + $\text{Ag}_2\text{Se} + \text{Ag}_3\text{AsSe}_3$, 6– $\text{Ag}_8\text{GeSe}_6 + \text{Ag}_3\text{AsSe}_3$

3.5 The Quasi-Binary System $\text{GeSe}_2 - \text{AgAsSe}_2$

Phase diagram of the $\text{GeSe}_2\text{--AgAsSe}_2$ system (Fig. 9) is based on DTA (Table 4), XRD and MSA results for 16 samples, compositions of which are given in Table 4. Phase diagram is of the eutectic type, the liquidus consists of the curves of the primary crystallization of GeSe_2 (*ab*) and the solid solution HTM-AgAsSe_2 (*bc*), respectively. The horizontal line at 670 K (397 °C) corresponds to the invariant eutectic reaction $\text{L}_{e6} \leftrightarrow \text{GeSe}_2 + \text{HTM-AgAsSe}_2$. The coordinates of the eutectic point e_6 are 7.7 mol.% $\text{GeSe}_2\text{--}92.3$ mol.% AgAsSe_2 (46 mol.% $\text{Ag}_2\text{Se}\text{--}8$ mol.% $\text{GeSe}_2\text{--}46$ mol.% As_2Se_3) as determined by plotting the Tammann triangle. The eutectoid reaction $\text{HTM-AgAsSe}_2 \leftrightarrow \text{LTM-AgAsSe}_2 + \text{GeSe}_2$ takes place at 610 K (337 °C). Below this temperature, the samples are two-phase $\text{GeSe}_2 + \text{LTM-AgAsSe}_2$ that is consistent with Fig. 2. No significant solid solubility based on the starting compounds was detected.

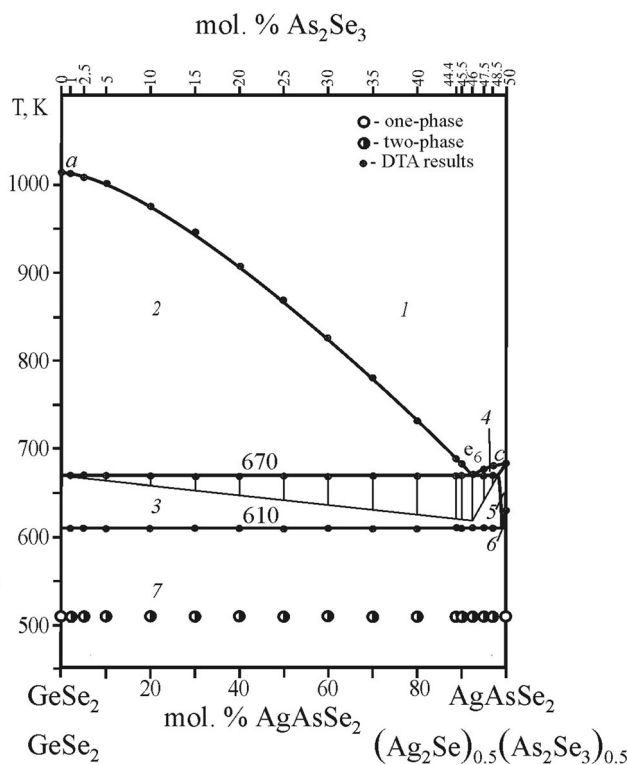


Fig. 9 Phase diagram of the $\text{GeSe}_2\text{--AgAsSe}_2$ system: 1–L, 2–L + GeSe_2 , 3– $\text{GeSe}_2 + \text{HTM-AgAsSe}_2$, 4–L + HTM-AgAsSe_2 , 5– HTM-AgAsSe_2 , 6– $\text{HTM-AgAsSe}_2 + \text{LTM-AgAsSe}_2$, 7– $\text{GeSe}_2 + \text{LTM-AgAsSe}_2$

3.6 The Vertical Section $\text{Ag}_8\text{GeSe}_6\text{--As}_2\text{Se}_3$

The $\text{Ag}_8\text{GeSe}_6 - \text{As}_2\text{Se}_3$ section (Fig. 10) is based on XRD, MSA and DTA results of 20 samples. Their compositions and DTA data are shown in Table 5. The liquidus of the vertical section is represented by the primary crystallization curves of Ag_8GeSe_6 (*ab*), GeSe_2 (*bcd*), HTM-AgAsSe_2 (*df*), AgAs_3Se_5 (*fg*) and As_2Se_3 (*g*). The section crosses two subsystems of the studied quasi-ternary system, $\text{AgAsSe}_2 + \text{Ag}_8\text{GeSe}_6 + \text{GeSe}_2$ (II) and $\text{AgAsSe}_2 + \text{GeSe}_2 + \text{As}_2\text{Se}_3$ (III). The section crosses the plane of the invariant eutectic reaction $\text{L}_{E2} \leftrightarrow \text{HTM-AgAsSe}_2 + \text{Ag}_8\text{GeSe}_6 + \text{AgAs}_3\text{Se}_5$ at 630 K (357 °C) in subsystem II. This ends with the exhaustion of liquid, therefore the alloys are three-phase (field 12) below 630 K (357 °C) in the region between 2 and 75 mol.% As_2Se_3 . The horizontal at 590 K (317 °C) represents the reaction $\text{HTM-AgAsSe}_2 \leftrightarrow \text{LTM-AgAsSe}_2 + \text{Ag}_8\text{GeSe}_6 + \text{GeSe}_2$ in the subsolidus region, and alloys below 590 K contain LTM-AgAsSe_2 and are three-phase ($\text{LTM-AgAsSe}_2 + \text{Ag}_8\text{GeSe}_6 + \text{GeSe}_2$).

Table 4 Compositions of the samples of the $\text{GeSe}_2\text{-AgAsSe}_2$ quasi-binary system calculated from the compositions of the ternary, binary compounds and their DTA results

| No | Composition, mol. % | T, K |
|----|---|------------------------|
| 1 | GeSe_2 | 1013 |
| 2 | 98 $\text{GeSe}_2\text{-}2 \text{ AgAsSe}_2$ ($\text{Ag}_2\text{Se-}98 \text{ GeSe}_2\text{-}2.5 \text{ As}_2\text{Se}_3$) | 1011 ; 670; 610 |
| 3 | 95 $\text{GeSe}_2\text{-}5 \text{ AgAsSe}_2$ ($2.5 \text{ Ag}_2\text{Se-}95 \text{ GeSe}_2\text{-}2.5 \text{ As}_2\text{Se}_3$) | 1007 ; 671; 610 |
| 4 | 90 $\text{GeSe}_2\text{-}10 \text{ AgAsSe}_2$ ($5 \text{ Ag}_2\text{Se-}90 \text{ GeSe}_2\text{-}5 \text{ As}_2\text{Se}_3$) | 1002 ; 670; 609 |
| 5 | 80 $\text{GeSe}_2\text{-}20 \text{ AgAsSe}_2$ ($10 \text{ Ag}_2\text{Se-}80 \text{ GeSe}_2\text{-}10 \text{ As}_2\text{Se}_3$) | 975 ; 670; 610 |
| 6 | 70 $\text{GeSe}_2\text{-}30 \text{ AgAsSe}_2$ ($15 \text{ Ag}_2\text{Se-}70 \text{ GeSe}_2\text{-}15 \text{ As}_2\text{Se}_3$) | 949 ; 669; 610 |
| 7 | 60 $\text{GeSe}_2\text{-}40 \text{ AgAsSe}_2$ ($20 \text{ Ag}_2\text{Se-}60 \text{ GeSe}_2\text{-}20 \text{ As}_2\text{Se}_3$) | 907 ; 669; 610 |
| 8 | 50 $\text{GeSe}_2\text{-}50 \text{ AgAsSe}_2$ ($25 \text{ Ag}_2\text{Se-}50 \text{ GeSe}_2\text{-}25 \text{ As}_2\text{Se}_3$) | 868 ; 669; 609 |
| 9 | 40 $\text{GeSe}_2\text{-}60 \text{ AgAsSe}_2$ ($30 \text{ Ag}_2\text{Se-}40 \text{ GeSe}_2\text{-}30 \text{ As}_2\text{Se}_3$) | 825 ; 669; 610 |
| 10 | 30 $\text{GeSe}_2\text{-}70 \text{ AgAsSe}_2$ ($35 \text{ Ag}_2\text{Se-}30 \text{ GeSe}_2\text{-}35 \text{ As}_2\text{Se}_3$) | 780 ; 670; 610 |
| 11 | 20 $\text{GeSe}_2\text{-}80 \text{ AgAsSe}_2$ ($40 \text{ Ag}_2\text{Se-}20 \text{ GeSe}_2\text{-}40 \text{ As}_2\text{Se}_3$) | 730 ; 670; 610 |
| 12 | 11.2 $\text{GeSe}_2\text{-}88.8 \text{ AgAsSe}_2$ ($44.4 \text{ Ag}_2\text{Se-}11.2 \text{ GeSe}_2\text{-}44.4 \text{ As}_2\text{Se}_3$) | 690 ; 670; 610 |
| 13 | 9 $\text{GeSe}_2\text{-}91 \text{ AgAsSe}_2$ ($45.5 \text{ Ag}_2\text{Se-}9 \text{ GeSe}_2\text{-}45.5 \text{ As}_2\text{Se}_3$) | 683 ; 670; 609 |
| 14 | 8 $\text{GeSe}_2\text{-}92 \text{ AgAsSe}_2$ ($46 \text{ Ag}_2\text{Se-}8 \text{ GeSe}_2\text{-}46 \text{ As}_2\text{Se}_3$) | 670 ; 610 |
| 15 | 5 $\text{GeSe}_2\text{-}95 \text{ AgAsSe}_2$ ($47.5 \text{ Ag}_2\text{Se-}5 \text{ GeSe}_2\text{-}47.5 \text{ As}_2\text{Se}_3$) | 676 ; 670; 610 |
| 16 | 3 $\text{GeSe}_2\text{-}97 \text{ AgAsSe}_2$ ($48.5 \text{ Ag}_2\text{Se-}3 \text{ GeSe}_2\text{-}48.5 \text{ As}_2\text{Se}_3$) | 680 ; 670; 610 |
| 17 | AgAsSe_2 | 683 ; 630 |
| | ($50 \text{ Ag}_2\text{Se-}0 \text{ GeSe}_2\text{-}50 \text{ As}_2\text{Se}_3$) | |

Bold values indicate the melting temperatures of the samples

The sample with 80 mol.% As_2Se_3 is two-phase at the annealing temperature ($\text{LTM-AgAsSe}_2 + \text{GeSe}_2$) because it falls on the quasi-binary section $\text{GeSe}_2\text{-AgAsSe}_2$. The section in subsystem III crosses the reaction plane at 634 K (361 °C) which reflects the invariant reaction $\text{L}_{\text{U}2} + \text{HTM-AgAsSe}_2 \leftrightarrow \text{AgAs}_3\text{Se}_5 + \text{GeSe}_2$. This reaction ends in samples with higher Ag_8GeSe_6 content with the disappearance of the liquid, so that the alloys of this subsystem below 634 K (361 °C) are three-phase (field 15). The horizontal line at 630 K (357 °C) corresponds to the

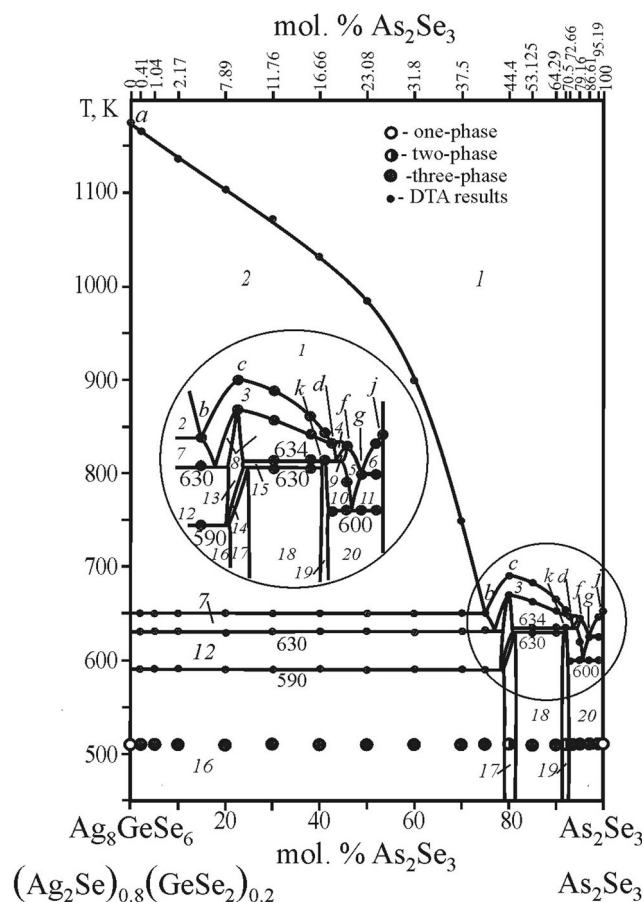


Fig. 10 The vertical section $\text{Ag}_8\text{GeSe}_6\text{-As}_2\text{Se}_3$: 1-L, 2-L + Ag_8GeSe_6 , 3-L + GeSe_2 , 4-L + HTM-AgAsSe_2 , 5-L + AgAs_3Se_5 , 6-L + As_2Se_3 , 7-L + $\text{Ag}_8\text{GeSe}_6 + \text{GeSe}_2$, 8-L + $\text{HTM-AgAsSe}_2 + \text{GeSe}_2$, 9-L + $\text{HTM-AgAsSe}_2 + \text{AgAs}_3\text{Se}_5$, 10-L + $\text{GeSe}_2 + \text{AgAs}_3\text{Se}_5$, 11-L + $\text{AgAs}_3\text{Se}_5 + \text{As}_2\text{Se}_3$, 12- $\text{Ag}_8\text{GeSe}_6 + \text{HTM-AgAsSe}_2 + \text{GeSe}_2$, 13- $\text{GeSe}_2 + \text{HTM-AgAsSe}_2$, 14- $\text{GeSe}_2 + \text{HTM-AgAsSe}_2 + \text{LTM-AgAsSe}_2$, 15- $\text{HTM-AgAsSe}_2 + \text{GeSe}_2 + \text{AgAs}_3\text{Se}_5$, 16- $\text{Ag}_8\text{GeSe}_6 + \text{LTM-AgAsSe}_2 + \text{GeSe}_2$, 17- $\text{GeSe}_2 + \text{LTM-AgAsSe}_2$, 18- $\text{LTM-AgAsSe}_2 + \text{GeSe}_2 + \text{AgAs}_3\text{Se}_5$, 19- $\text{GeSe}_2 + \text{AgAs}_3\text{Se}_5$, 20- $\text{GeSe}_2 + \text{AgAs}_3\text{Se}_5 + \text{As}_2\text{Se}_3$

reaction $\text{HTM-AgAsSe}_2 + \text{AgAs}_3\text{Se}_5 \leftrightarrow \text{LTM-AgAsSe}_2 + \text{GeSe}_2$ in the subsolidus region, thus the alloys below 630 K (357 °C) contain LTM-AgAsSe_2 and are three-phase ($\text{AgAs}_3\text{Se}_5 + \text{LTM-AgAsSe}_2 + \text{GeSe}_2$). This reaction ends in point *k* with the exhaustion of both L and HTM-AgAsSe_2 , so that the alloys are two-phase $\text{GeSe}_2 + \text{AgAs}_3\text{Se}_5$ below 630 K (357 °C) (field 19). Samples with higher As_2Se_3 content end in the invariant reaction at 634 K (361 °C) with the exhaustion of HTM-AgAsSe_2 . Therefore, the alloys below 634 K (361 °C) are three-phase L + $\text{GeSe}_2 + \text{AgAs}_3\text{Se}_5$ (field 10). This field together with the region of the secondary crystallization L + $\text{As}_2\text{Se}_3 + \text{AgAs}_3\text{Se}_5$ (field 11) descends to the plane

Table 5 Compositions of the samples of the $\text{Ag}_8\text{GeSe}_6 - \text{As}_2\text{Se}_3$ vertical section calculated from the compositions of the ternary, binary compounds and their DTA results

| No | Composition, mol. % | T, K |
|----|--|-----------------------------|
| 1 | Ag_8GeSe_6 (80 Ag_2Se –20 GeSe_2 –0 As_2Se_3) | 1175 |
| 2 | 98 Ag_8GeSe_6 –2 As_2Se_3 (79.67 Ag_2Se –19.92 GeSe_2 –0.41 As_2Se_3) | 1165 ; 650; 630; 590 |
| 3 | 95 Ag_8GeSe_6 –5 As_2Se_3 (79.17 Ag_2Se –19.79 GeSe_2 –1.04 As_2Se_3) | -; 650; 630; 590 |
| 4 | 90 Ag_8GeSe_6 –10 As_2Se_3 (78.26 Ag_2Se –19.57 GeSe_2 –2.17 As_2Se_3) | 1135 ; 650; 630; 591 |
| 5 | 80 Ag_8GeSe_6 –20 As_2Se_3 (76.19 Ag_2Se –19.05 GeSe_2 –4.76 As_2Se_3) | 1100 ; 650; 629; 590 |
| 6 | 70 Ag_8GeSe_6 –30 As_2Se_3 (73.68 Ag_2Se –18.43 GeSe_2 –7.89 As_2Se_3) | 1070 ; 650; 630; 590 |
| 7 | 60 Ag_8GeSe_6 –40 As_2Se_3 (70.59 Ag_2Se –17.65 GeSe_2 –11.76 As_2Se_3) | 1030 ; 650; 630; 591 |
| 8 | 50 Ag_8GeSe_6 –50 As_2Se_3 (66.67 Ag_2Se –16.67 GeSe_2 –16.66 As_2Se_3) | 985 ; 650; 630; 589 |
| 9 | 40 Ag_8GeSe_6 –60 As_2Se_3 (61.54 Ag_2Se –15.38 GeSe_2 –23.08 As_2Se_3) | 900 ; 650; 630; 590 |
| 10 | 30 Ag_8GeSe_6 –70 As_2Se_3 (54.54 Ag_2Se –13.64 GeSe_2 –31.82 As_2Se_3) | 750 ; 650; 630; 590 |
| 11 | 25 Ag_8GeSe_6 –75 As_2Se_3 (50 Ag_2Se –12.5 GeSe_2 –37.5 As_2Se_3) | 650 ; 631; 590 |
| 12 | 20 Ag_8GeSe_6 –80 As_2Se_3 (44.4 Ag_2Se –11.2 GeSe_2 –44.4 As_2Se_3) | 690 ; 670; - |
| 13 | 15 Ag_8GeSe_6 –85 As_2Se_3 (37.5 Ag_2Se –9.375 GeSe_2 –53.125 As_2Se_3) | 682 ; 663; 634; 630 |
| 14 | 10 Ag_8GeSe_6 –90 As_2Se_3 (28.57 Ag_2Se –7.14 GeSe_2 –64.29 As_2Se_3) | 665 ; 652; 634; 630 |
| 15 | 7.7 Ag_8GeSe_6 –92.3 As_2Se_3 (23.5 Ag_2Se –6 GeSe_2 –70.5 As_2Se_3) | 653 ; -, 634 |
| 16 | 7 Ag_8GeSe_6 –93 As_2Se_3 (21.87 Ag_2Se –5.47 GeSe_2 –72.66 As_2Se_3) | 645 ; -, 600 |
| 17 | 5 Ag_8GeSe_6 –95 As_2Se_3 (16.67 Ag_2Se –4.17 GeSe_2 –79.16 As_2Se_3) | 644 ; 620; 600 |
| 18 | 3 Ag_8GeSe_6 –97 As_2Se_3 (10.71 Ag_2Se –2.68 GeSe_2 –86.61 As_2Se_3) | 625 ; 600 |
| 19 | 1 Ag_8GeSe_6 –99 As_2Se_3 (3.85 Ag_2Se –0.96 GeSe_2 –95.19 As_2Se_3) | 645 ; 625; 600 |
| 20 | As_2Se_3 | 652 |

Bold values indicate the melting temperatures of the samples

of the invariant reaction $\text{L}_{\text{E}3} \leftrightarrow \text{GeSe}_2 + \text{As}_2\text{Se}_3 + \text{AgAs}_3\text{Se}_5$ at 600 K (327 °C). This reaction ends with the exhaustion of the liquid; thus, the alloys are three-phase ($\text{GeSe}_2 + \text{As}_2\text{Se}_3 + \text{AgAs}_3\text{Se}_5$) below 600 K (327 °C).

This agrees with the results shown in Fig. 2. The phase composition of the samples was determined by XRD and MSA results.

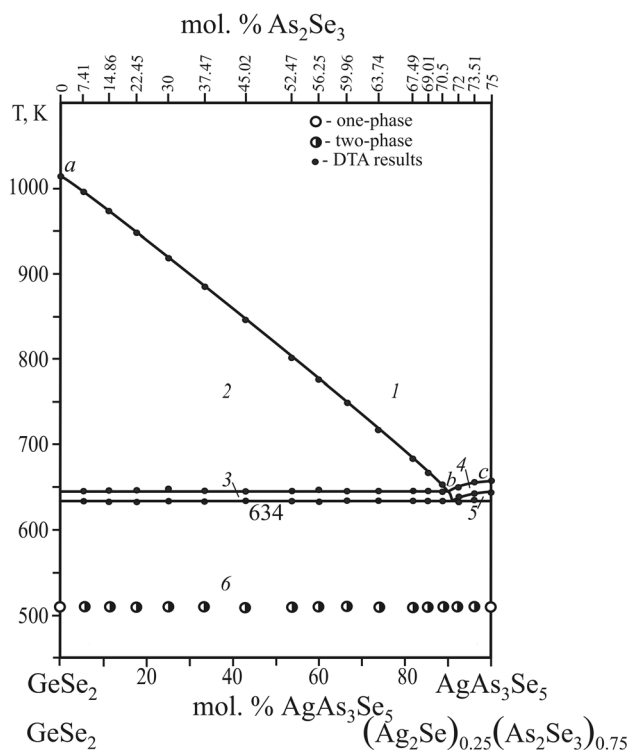


Fig. 11 The vertical section $\text{GeSe}_2\text{-AgAs}_3\text{Se}_5$: 1–L, 2–L + GeSe_2 , 3–L + HTM- AgAsSe_2 + GeSe_2 , 4–L + HTM- AgAsSe_2 , 5–L + HTM- AgAsSe_2 + AgAs_3Se_5 , 6– $\text{GeSe}_2\text{-AgAs}_3\text{Se}_5$

3.7 The Vertical Section $\text{GeSe}_2\text{-AgAs}_3\text{Se}_5$

The section (Fig. 11) was investigated by DTA, XRD and MSA of 17 samples with compositions given in Table 6. The liquidus consists of the curves of the primary crystallization of GeSe_2 (*ab*) and HTM- AgAsSe_2 (*bc*). The section crosses the plane of the invariant reaction $\text{L}_{\text{U}_2} + \text{HTM-}\text{AgAsSe}_2 \leftrightarrow \text{AgAs}_3\text{Se}_5 + \text{GeSe}_2$ at 634 K (361 °C), which ends with the exhaustion of both L and HTM- AgAsSe_2 , so that the alloys are two-phase below 634 K (361 °C) as confirmed by XRD and MSA results.

3.8 Liquidus Surface Projection of the Quasi-Ternary System $\text{Ag}_2\text{Se-GeSe}_2\text{-As}_2\text{Se}_3$

The liquidus surface projection of the quasi-ternary system $\text{Ag}_2\text{Se-GeSe}_2\text{-As}_2\text{Se}_3$ (Fig. 12 and Table 7) is based on literature data and our own results from studies of three phase diagrams $\text{Ag}_2\text{Se-As}_2\text{Se}_3$, $\text{Ag}_8\text{GeSe}_6\text{-AgAsSe}_2$ and $\text{GeSe}_2\text{-AgAsSe}_2$ and three vertical sections $\text{Ag}_8\text{GeSe}_6\text{-Ag}_3\text{AsSe}_3$, $\text{Ag}_8\text{GeSe}_6\text{-As}_2\text{Se}_3$ and $\text{GeSe}_2\text{-AgAs}_3\text{Se}_5$, as well as the isothermal section of the system at 513 K (240 °C).

Table 6 Compositions of the samples of the $\text{GeSe}_2\text{-AgAs}_3\text{Se}_5$ vertical section calculated from the compositions of the ternary, binary compounds and their DTA results

| No | Composition, mol. % | T, K |
|----|---|-----------------------|
| 1 | GeSe_2 | 1013 |
| 2 | 94.8 $\text{GeSe}_2\text{-5.2 AgAs}_3\text{Se}_5$ (2.47 $\text{Ag}_2\text{Se-90.11 GeSe}_2\text{-7.41 As}_2\text{Se}_3$) | 995 ; 645; 634 |
| 3 | 89 $\text{GeSe}_2\text{-11 AgAs}_3\text{Se}_5$ (4.95 $\text{Ag}_2\text{Se-80.18 GeSe}_2\text{-14.86 As}_2\text{Se}_3$) | 973 ; 646; 633 |
| 4 | 82.4 $\text{GeSe}_2\text{-17.6 AgAs}_3\text{Se}_5$ (7.48 $\text{Ag}_2\text{Se-70.07 GeSe}_2\text{-22.45 As}_2\text{Se}_3$) | 947 ; 647; 633 |
| 5 | 75 $\text{GeSe}_2\text{-25 AgAs}_3\text{Se}_5$ (10 $\text{Ag}_2\text{Se-60 GeSe}_2\text{-30 As}_2\text{Se}_3$) | 917 ; 648; 634 |
| 6 | 66.7 $\text{GeSe}_2\text{-33.3 AgAs}_3\text{Se}_5$ (12.49 $\text{Ag}_2\text{Se-50.04 GeSe}_2\text{-37.47 As}_2\text{Se}_3$) | 885 ; 645; 634 |
| 7 | 57.2 $\text{GeSe}_2\text{-42.8 AgAs}_3\text{Se}_5$ (14.97 $\text{Ag}_2\text{Se-40.01 GeSe}_2\text{-45.02 As}_2\text{Se}_3$) | 845 ; 645; 634 |
| 8 | 46.2 $\text{GeSe}_2\text{-53.8 AgAs}_3\text{Se}_5$ (17.49 $\text{Ag}_2\text{Se-30.04 GeSe}_2\text{-52.47 As}_2\text{Se}_3$) | 801 ; 645; 634 |
| 9 | 40 $\text{GeSe}_2\text{-60 AgAs}_3\text{Se}_5$ (18.75 $\text{Ag}_2\text{Se-25 GeSe}_2\text{-56.25 As}_2\text{Se}_3$) | 775 ; 646; 633 |
| 10 | 33.4 $\text{GeSe}_2\text{-66.6 AgAs}_3\text{Se}_5$ (19.99 $\text{Ag}_2\text{Se-20.05 GeSe}_2\text{-59.96 As}_2\text{Se}_3$) | 750 ; 645; 634 |
| 11 | 26.1 $\text{GeSe}_2\text{-73.9 AgAs}_3\text{Se}_5$ (21.25 $\text{Ag}_2\text{Se-15.01 GeSe}_2\text{-63.74 As}_2\text{Se}_3$) | 717 ; 645; 634 |
| 12 | 18.2 $\text{GeSe}_2\text{-81.8 AgAs}_3\text{Se}_5$ (22.5 $\text{Ag}_2\text{Se-10.01 GeSe}_2\text{-67.49 As}_2\text{Se}_3$) | 683 ; 645; 634 |
| 13 | 14.8 $\text{GeSe}_2\text{-85.2 AgAs}_3\text{Se}_5$ (23.0 $\text{Ag}_2\text{Se-7.99 GeSe}_2\text{-69.01 As}_2\text{Se}_3$) | 667 ; 645; 634 |
| 14 | 11.3 $\text{GeSe}_2\text{-88.7 AgAs}_3\text{Se}_5$ (23.5 $\text{Ag}_2\text{Se-6 GeSe}_2\text{-70.5 As}_2\text{Se}_3$) | 653 ; 645; 634 |
| 15 | 7.7 $\text{GeSe}_2\text{-92.3 AgAs}_3\text{Se}_5$ (24 $\text{Ag}_2\text{Se-4 GeSe}_2\text{-72 As}_2\text{Se}_3$) | 650 ; 638; 634 |
| 16 | 3.9 $\text{GeSe}_2\text{-96.1 AgAs}_3\text{Se}_5$ (24.5 $\text{Ag}_2\text{Se-1.99 GeSe}_2\text{-73.51 As}_2\text{Se}_3$) | 655 ; 642; 635 |
| 17 | AgAs_3Se_5 (25 $\text{Ag}_2\text{Se-75 As}_2\text{Se}_3$) | 657 ; 644 |

Bold values indicate the melting temperatures of the samples

The system's liquidus consists of the fields of the primary crystallization of Ag_2Se ($\text{Ag}_2\text{Se-p}_2\text{-U}_1\text{-e}_3\text{-Ag}_2\text{Se}$), Ag_3AsSe_3 ($\text{e}_2\text{-E}_1\text{-U}_1\text{-p}_2\text{-e}_2$), HTM- AgAsSe_2 ($\text{p}_1\text{-U}_2\text{-e}_6\text{-E}_2\text{-e}_5\text{-E}_1\text{-e}_2\text{-p}_1$), AgAs_3Se_5 ($\text{e}_1\text{-E}_3\text{-U}_2\text{-p}_1\text{-e}_1$), As_2Se_3 ($\text{As}_2\text{Se}_3\text{-e}_7\text{-E}_3\text{-e}_1\text{-As}_2\text{Se}_3$), Ag_8GeSe_6 ($\text{e}_3\text{-U}_1\text{-E}_1\text{-e}_5\text{-E}_2\text{-e}_4\text{-e}_3$) and GeSe_2 ($\text{GeSe}_2\text{-e}_7\text{-E}_3\text{-U}_2\text{-e}_6\text{-E}_2\text{-e}_4\text{-GeSe}_2$). The largest fields correspond to the primary crystallization of Ag_8GeSe_6 and GeSe_2 . The fields of the primary crystallization are

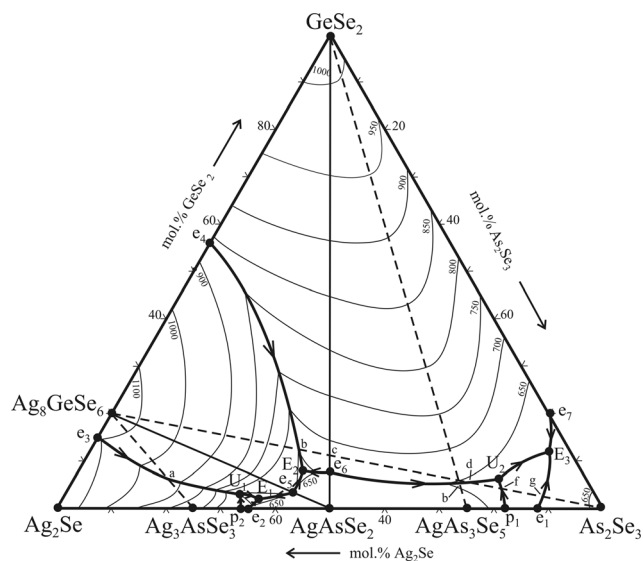


Fig. 12 Liquidus surface projection of the quasi-ternary system $Ag_2Se-GeSe_2-As_2Se_3$

separated by 13 monovariant curves of binary eutectic and peritectic reactions and 14 invariant points (Table 7).

The system undergoes five quaternary invariant reactions (Table 7): transition $L_{U1} + Ag_2Se \leftrightarrow Ag_8GeSe_6 + Ag_3AsSe_3$ at 650 K (377 °C), eutectic $L_{E1} \leftrightarrow Ag_8GeSe_6 + Ag_3AsSe_3 + HTM-AgAsSe_2$ at 640 K (367 °C), eutectic $L_{E2} \leftrightarrow Ag_8GeSe_6 + GeSe_2 + HTM-AgAsSe_2$ at 630 K (357 °C), transition $L_{U2} + HTM-AgAsSe_2 \leftrightarrow AgAs_3Se_5 + GeSe_2$ at 634 K

(361 °C) and eutectic $L_{E3} \leftrightarrow GeSe_2 + As_2Se_3 + AgAs_3Se_5$ at 600 K (327 °C).

4 Conclusions and Future Work

Phase equilibria in the $Ag_2Se-GeSe_2-As_2Se_3$ system were investigated for the first time by XRD and MSA. At 513 K (240 °C) four ternary compounds Ag_8GeSe_6 , Ag_3AsSe_3 , $AgAs_3Se_5$, $AgAs_3Se_5$ were identified and an isothermal section of $Ag_2Se-GeSe_2-As_2Se_3$ system was constructed. The liquidus surface projection of the quasi-ternary system $Ag_2Se-GeSe_2-As_2Se_3$ was plotted according to the investigation of the vertical sections $Ag_8GeSe_6-Ag_3AsSe_3$, $Ag_8GeSe_6-As_2Se_3$, $GeSe_2-AgAs_3Se_5$ and phase diagrams $Ag_2Se-As_2Se_3$, $Ag_8GeSe_6-AgAs_3Se_5$, $GeSe_2-AgAs_3Se_5$. There are seven fields of the primary crystallization of Ag_2Se , Ag_3AsSe_3 , HTM- $AgAs_3Se_5$, $AgAs_3Se_5$, As_2Se_3 , Ag_8GeSe_6 and $GeSe_2$ on the liquidus surface projection with the largest fields of Ag_8GeSe_6 and $GeSe_2$ compounds. In the investigated system there are two transition reactions: $L_{U1} + Ag_2Se \leftrightarrow Ag_8GeSe_6 + Ag_3AsSe_3$ at 650 K (377 °C), $L_{U2} + HTM-AgAs_3Se_5 \leftrightarrow AgAs_3Se_5 + GeSe_2$ at 634 K (361 °C) and three eutectic ones: $L_{E1} \leftrightarrow Ag_8GeSe_6 + Ag_3AsSe_3 + HTM-AgAs_3Se_5$ at 640 K (367 °C), $L_{E2} \leftrightarrow Ag_8GeSe_6 + GeSe_2 + HTM-AgAs_3Se_5$ at 630 K (357 °C) and $L_{E3} \leftrightarrow GeSe_2 + As_2Se_3 + AgAs_3Se_5$ at 600 K (327 °C).

This work was performed as part of the effort to gather more data for a thermodynamic assessment of the Ag_2Se-

Table 7 Character, temperatures of invariant reactions and coordinates of invariant points in the quasi-ternary system $Ag_2Se-GeSe_2-As_2Se_3$

| Invariant point | Process | T, K (T, °C) | Composition, mol.% | | |
|-----------------|---|-----------------|--------------------|----------|------------|
| | | | Ag_2Se | $GeSe_2$ | As_2Se_3 |
| e_1 | $L \leftrightarrow AgAs_3Se_5 + As_2Se_3$ | 635 (362) | 12 | 0 | 88 |
| e_2 | $L \leftrightarrow Ag_3AsSe_3 + HTM-AgAsSe_2$ | 655 (382) | 65 | 0 | 35 |
| e_3 | $L \leftrightarrow Ag_8GeSe_6 + Ag_2Se$ | 1103 (830) | 85 | 15 | 0 |
| e_4 | $L \leftrightarrow Ag_8GeSe_6 + GeSe_2$ | 843 (570) | 44 | 56 | 0 |
| e_5 | $L \leftrightarrow Ag_8GeSe_6 + HTM-AgAsSe_2$ | 660 (387) | 55.2 | 3.4 | 41.4 |
| e_6 | $L \leftrightarrow GeSe_2 + HTM-AgAsSe_2$ | 670 (397) | 46 | 8 | 46 |
| e_7 | $L \leftrightarrow GeSe_2 + As_2Se_3$ | 618 (345) | 0 | 20 | 80 |
| p_1 | $L + HTM-AgAsSe_2 \leftrightarrow AgAs_3Se_5$ | 644 (371) | 18 | 0 | 82 |
| p_2 | $L + Ag_2Se \leftrightarrow Ag_3AsSe_3$ | 660 (387) | 66 | 0 | 34 |
| U_1 | $L_{U1} + Ag_2Se \leftrightarrow Ag_8GeSe_6 + Ag_3AsSe_3$ | 650 (377) | 65 | 3 | 32 |
| U_2 | $L_{U2} + HTM-AgAsSe_2 \leftrightarrow AgAs_3Se_5 + GeSe_2$ | 634 (361) | 16 | 6 | 78 |
| E_1 | $L_{E1} \leftrightarrow Ag_8GeSe_6 + Ag_3AsSe_3 + HTM-AgAsSe_2$ | 640 (367) | 62 | 2 | 36 |
| E_2 | $L_{E2} \leftrightarrow Ag_8GeSe_6 + GeSe_2 + HTM-AgAsSe_2$ | 630 (357) | 51 | 8 | 41 |
| E_3 | $L_{E3} \leftrightarrow GeSe_2 + As_2Se_3 + AgAs_3Se_5$ | 600 (327) | 4 | 12 | 84 |

$B^{IV}Se_2-As_2Se_3$ systems, where $B^{IV}-Si, Ge, Sn$, which is still in progress.

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